

# Homework #8

## Solutions

1.  $n_v/N = 3.091 \times 10^{-5}$  at  $1234^\circ\text{C} = 1507\text{ K}$   
 $= 5.26 \times 10^{-3}$  at  $\text{mp} = 2716\text{ K}$

$$\frac{n_v}{N} = A \exp\left(-\frac{\Delta H_v}{RT}\right)$$

$$3.091 \times 10^{-5} = A \exp - \frac{\Delta H_v}{1507 R} \quad (1)$$

$$5.26 \times 10^{-3} = A \exp - \frac{\Delta H_v}{2716 R} \quad (2)$$

$$(1)/(2) = 5.876 \times 10^{-3} = \exp\left(-\frac{\Delta H_v}{1507 R} + \frac{\Delta H_v}{2716 R}\right)$$

Taking the logarithm of both sides gives

$$-5.137 = \frac{\Delta H_v}{R} \left(-\frac{1}{1507} + \frac{1}{2716}\right) = -2.954 \times 10^{-4} \frac{\Delta H_v}{R} \Rightarrow \Delta H_v = 1.497 \times 10^5 \text{ J/mol}$$

| $2\theta$ | $\sin^2\theta$ | normalized | clear fractions | (hkl)? | $\frac{\sin^2 \theta}{h^2 + k^2 + l^2}$ |
|-----------|----------------|------------|-----------------|--------|---|
| 38.40     | 0.108          | 1.00       | 3               | 111    | 0.0360                                  |
| 44.50     | 0.143          | 1.32       | 4               | 200    | 0.0358                                  |
| 64.85     | 0.288          | 2.67       | 8               | 220    | 0.0359                                  |
| 77.90     | 0.395          | 3.66       | 11              | 311    | 0.0358                                  |
| 81.85     | 0.429          | 3.97       | 12              | 222    | 0.0358                                  |
| 98.40     | 0.573          | 5.31       | 16              | 400    | 0.0358                                  |
| 111.20    | 0.681          | 6.31       | 19              | 331    | 0.0358                                  |

2. All we need to know is the temperature dependence of the vacancy density:

$$\frac{n_v}{N} = Ae^{-\frac{\Delta H_v}{RT}} \quad \text{where } T \text{ is in Kelvins and the m.p. of Al is } 660^\circ\text{C}$$

$$\frac{0.08}{100} = Ae^{-\Delta H_v/RT_1}, \text{ where } T_1 = 923\text{K}; \quad \frac{0.01}{100} = Ae^{-\Delta H_v/RT_2}, \text{ where } T_2 = 757\text{K}$$

Taking the ratio:

$$\frac{8 \times 10^{-4}}{1 \times 10^{-4}} = \frac{Ae^{-\Delta H_v/RT_1}}{Ae^{-\Delta H_v/RT_2}} = e^{-\frac{\Delta H_v}{R} \left( \frac{1}{T_1} - \frac{1}{T_2} \right)} \quad \therefore \ln 8 = -\frac{\Delta H_v}{R} \left( \frac{1}{T_1} - \frac{1}{T_2} \right)$$

$$\therefore \Delta H_v = -\frac{R \times \ln 8}{\frac{1}{923} - \frac{1}{757}} = -\frac{8.314 \times \ln 8}{\frac{1}{923} - \frac{1}{757}} = 7.28 \times 10^4 \text{ J/mole vac}$$

$$\therefore \Delta H_v = \frac{7.28 \times 10^4}{6.02 \times 10^{23}} = 1.21 \times 10^{-19} \text{ J/vac} = 0.755 \text{ eV/vac}$$

- 3.(a) We need to know the temperature dependence of the vacancy density:

$$\frac{1}{10^4} = Ae^{-\frac{\Delta H_v}{kT_1}} \quad \text{and} \quad \frac{1}{10^3} = Ae^{-\frac{\Delta H_v}{kT_x}}$$

$$\text{From the ratio: } \frac{\frac{1}{10^4}}{\frac{1}{10^3}} = \frac{10^3}{10^4} = \frac{Ae^{-\Delta H_v/kT_1}}{Ae^{-\Delta H_v/kT_x}} \quad \text{we get } -\ln 10 = -\frac{\Delta H_v}{k} \left( \frac{1}{T_1} - \frac{1}{T_x} \right)$$

$$\therefore \left( \frac{1}{T_1} - \frac{1}{T_x} \right) = \frac{k \ln 10}{\Delta H_v}$$

$$\frac{1}{T_x} = \frac{1}{T_1} - \frac{k \ln 10}{\Delta H_v} = \frac{1}{1073} - \frac{1.38 \times 10^{-23} \times \ln 10}{2 \times 1.6 \times 10^{-19}} = 8.33 \times 10^{-4}$$

$$T_x = 1200 \text{ K} = 928^\circ\text{C}$$

- (b) repeat the calculation following the method given above but with  $\Delta H_v = 1.0 \text{ eV}$  to find that  $T_x = 1364 \text{ K} = 1091^\circ\text{C}$

NOTE: the change in  $\Delta H_v$  from 2.0 eV to 1.0 eV resulted in a change from 128 K to 291 K in  $\Delta T$ .

4. Cu is FCC; example: (111)  $[10\bar{1}]$ ; (111)  $[\bar{1}01]$ ;  $(\bar{1}\bar{1}\bar{1}) [0\bar{1}1]$ ;  $(\bar{1}\bar{1}\bar{1}) [\bar{1}01]$
- 5.

| Defect | Type           | Improved Materials Properties | Adversely Affected Materials Properties |
|--------|----------------|-------------------------------|---|
|        | Vacancy $f(T)$ | - diffusivity                 | - electron mobility                     |

|               |                  |  |   |
|---------------|------------------|--|---|
| Point Defect  |                  | – color centers<br>– ionic conductivity  | – carrier lifetime  |
|               | Substitutional   | – conductivity (dopant)<br>– strength (hardness)<br>– characteristic T (like $T_M$ ) | – conductivity (impurities)<br>– ductility<br>– characteristic T        |
|               | Interstitial     | – strength<br>– characteristic T<br>– electrical properties                          | – ductility<br>– characteristic T<br>– electrical properties            |
| Line Defect   | Dislocation      | – ductility (malleability)<br>– strength (at high dislocation density)               | – strength<br>– yield stress<br>– optical properties<br>– lasing action |
| Planar Defect | Grain Boundaries | – strength   | – creep resistance<br>– electrical properties<br>– magnetic properties  |

6.  $\frac{n_v}{N} = A \exp\left(-\frac{\Delta H_v}{k_B T}\right), \quad \Delta H_v = 1.5 \text{ eV} \quad \frac{n_v}{N} = \frac{1}{10^6} \text{ at } 888^\circ\text{C}$

need first to solve for value of A -- use data at  $888^\circ\text{C}$

$$A = \frac{\frac{n_v}{N}}{\exp\left(-\frac{\Delta H_v}{k_B T}\right)} = \frac{10^{-6}}{\exp\left(-\frac{1.5 \times 1.6 \times 10^{-19}}{1.38 \times 10^{-23} \times (888 + 273)}\right)} = 3.203$$

calculate  $\frac{n_v}{N}$  at m.p. of Pd, 1825 K

$$\therefore \frac{n_v}{N} = 3.203 \times \exp\left(-\frac{1.5 \times 1.6 \times 10^{-19}}{1.38 \times 10^{-23} \times 1825}\right) = 2.328 \times 10^{-4} < 10^{-3}$$

$\therefore$  it is **not** possible to achieve a vacancy fraction of  $10^{-3}$  by simply raising temperature.